

## SOT-89 Plastic-Encapsulate Transistors

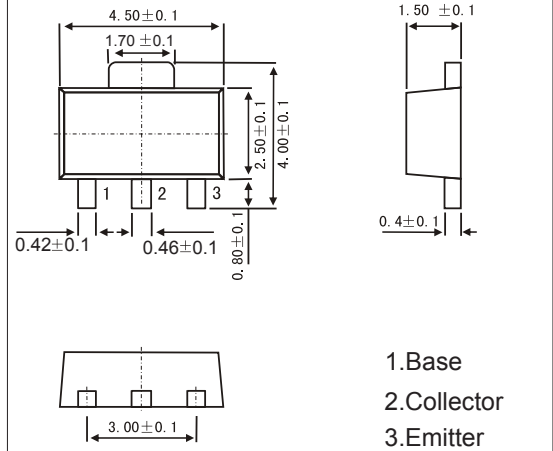
### Features

- Switching and Linear Amplification
- High Current and Low Voltage
- Complement to PXT2222A
- PNP Transistors

### MECHANICAL DATA

- Case style: SOT-89 molded plastic
- Mounting position: any

SOT-89



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CB0</sub>	-60	V
Collector - Emitter Voltage	V <sub>CEO</sub>	-60	
Emitter - Base Voltage	V <sub>EB0</sub>	-5	
Collector Current - Continuous	I <sub>c</sub>	-600	mA
Collector Power Dissipation	P <sub>c</sub>	500	mW
Thermal Resistance From Junction To Ambient	R <sub>θJA</sub>	250	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to 150	

### PACKAGE INFORMATION

Device	Package	Shipping
PXT2907A (KXT2907A)	SOT-89	1000/Tape&Reel

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>CB0</sub>	I <sub>c</sub> = -1 mA, I <sub>E</sub> = 0	-60			V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>c</sub> = -10 mA, I <sub>B</sub> = 0	-60			
Emitter-base breakdown voltage	V <sub>EB0</sub>	I <sub>E</sub> = -1 mA, I <sub>c</sub> = 0	-5			
Collector-base cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -50 V, I <sub>E</sub> = 0			-50	nA
Emitter cut-off current	I <sub>EB0</sub>	V <sub>EB</sub> = -5 V, I <sub>c</sub> = 0			-50	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> = -500 mA, I <sub>B</sub> = -50 mA			-1.6	V
		I <sub>c</sub> = -500 mA, I <sub>B</sub> = -15 mA			-0.4	
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> = -500 mA, I <sub>B</sub> = -50 mA			-2.6	
		I <sub>c</sub> = -500 mA, I <sub>B</sub> = -15 mA			-1.3	
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = -10V, I <sub>c</sub> = -0.1mA	75			
	h <sub>FE(2)</sub>	V <sub>CE</sub> = -10V, I <sub>c</sub> = -1mA	100			
	h <sub>FE(3)</sub>	V <sub>CE</sub> = -10V, I <sub>c</sub> = -10mA	100			
	h <sub>FE(4)</sub>	V <sub>CE</sub> = -10V, I <sub>c</sub> = -150mA	100		300	
	h <sub>FE(5)</sub>	V <sub>CE</sub> = -10V, I <sub>c</sub> = -500mA	50			
Delay time	t <sub>d</sub>	V <sub>CC</sub> = -30V, I <sub>c</sub> = -150mA I <sub>B1</sub> = -I <sub>B2</sub> = -15mA			12	ns
Rise time	t <sub>r</sub>				30	
Storage time	t <sub>s</sub>				300	
Fall time	t <sub>f</sub>				65	
Transition frequency	f <sub>T</sub>		V <sub>CE</sub> = -10V, I <sub>c</sub> = -20mA, f = 100MHz	200		

### Marking

Marking	*2F
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